

NANO AND MICROSCALE PARTICLE REMOVAL

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OUTLINE

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 - ❖ ***Particle Removal Mechanism***
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- ❑ ***Key Preliminary Research Results***

Surface Preparation Technology Requirements -- Long Term**

| YEAR | 1999 | 2000 | 2002 | 2005 | 2008 | 2011 | 2014 |
|--|--------------|------|--------------|--------------|-------------|-------------|-------------|
| TECHNOLOGY NODE | 180nm | | 130nm | 100nm | 70nm | 50nm | 35nm |
| FEOL Particle Size(nm) | 90 | 82.5 | 60 | 50 | 35 | 25 | 18 |
| FEOL Particles (#/cm ²) | 0.064 | 0.06 | 0.064 | 0.051 | 0.052 | 0.052 | 0.052 |
| BEOL Particle Size(nm) | 180 | 165 | 130 | 100 | 70 | 50 | 36 |
| BEOL Particles (#/cm ²) | 0.064 | 0.06 | 0.064 | 0.051 | 0.052 | 0.052 | 0.052 |
| Surface Roughness (nm) | 0.15 | 0.14 | 0.12 | 0.1 | 0.08 | 0.08 | 0.08 |
| Critical surface metals(*10 ⁹) | 9 | 7 | 4.4 | 2.5 | -- | -- | -- |
| Organics (*10 ¹³ atoms/cm ²) | 7.3 | 6.6 | 5.3 | 4.1 | -- | -- | -- |

** ---- The International Technology Roadmap for Semiconductors, 2000

Goals and Objectives

- ◆ **Develop an effective nanoscale particle removal technique using acoustic streaming.**
- ◆ **Provide a fundamental understanding of the removal mechanism that will be experimentally verified.**
- ◆ **Experimentally measure particle removal of particles in the size range of 10-100 nm from semiconductor wafers.**
- ◆ **Evaluate effect of streaming flow frequency, velocity amplitude and particle size and particle/substrate composition on the removal efficiency experimentally and numerically.**

Approach

- ◆ ***Fundamental Approach***
- ◆ ***Experimental and modeling approach to determine, understand and predict:***
 - ◆ ***Particle Removal Mechanism***
 - ◆ ***Cleaning Efficiency, $F\{R, V, F_{ad}, \text{etc.}\}$***
 - ◆ ***Cleaning tank Geometry (single, batch, etc.)***
 - ◆ ***Optimum cleaning conditions***
 - ◆ ***Cleaning technology limits with shrinking particle and defect size***

Approach

- ◆ ***Fundamental Approach***
- ◆ **Key Particle Removal Parameters**
 - ◆ flow frequency
 - ◆ velocity (pressure) amplitude
 - ◆ Particle size
 - ◆ Particle composition
 - ◆ Particle shape
 - ◆ Particle deformation and contact area
 - ◆ Double layer effect on removal
 - ◆ Cleaning liquid surface tension
 - ◆ Surface and particle surface energy (hydrophilic or hydrophobic)

MEGASONIC CLEANING

□ Megasonic sound wave:

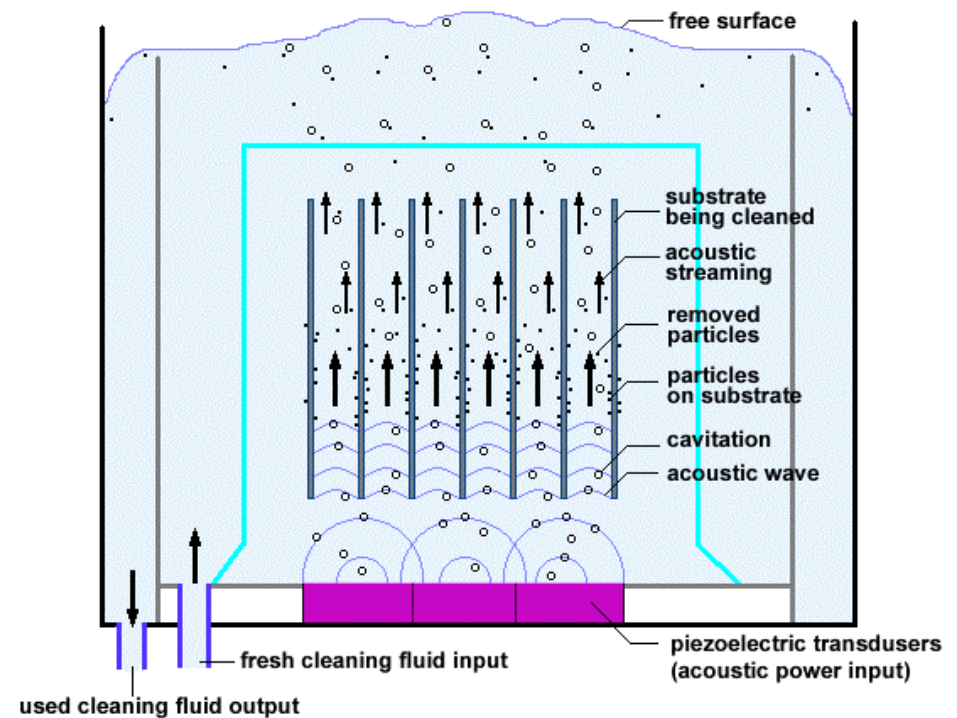
$$\tilde{N}^2 p = \frac{1}{c^2} \frac{\partial^2 p}{\partial t^2}$$

$$p(x, t) = p_0 \sin(kx - \omega t + F)$$

$$u(x, t) = u_0 \sin(kx - \omega t + F)$$

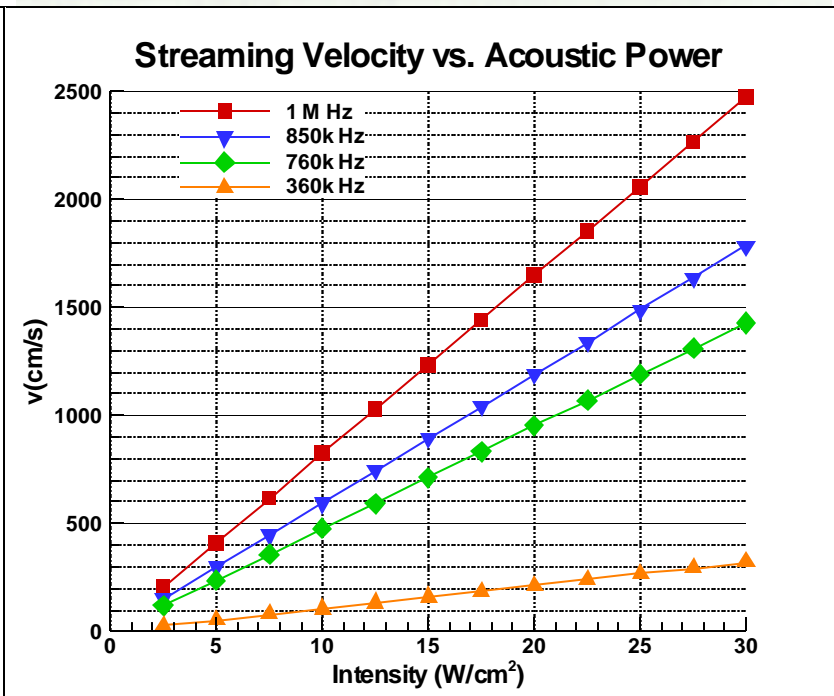
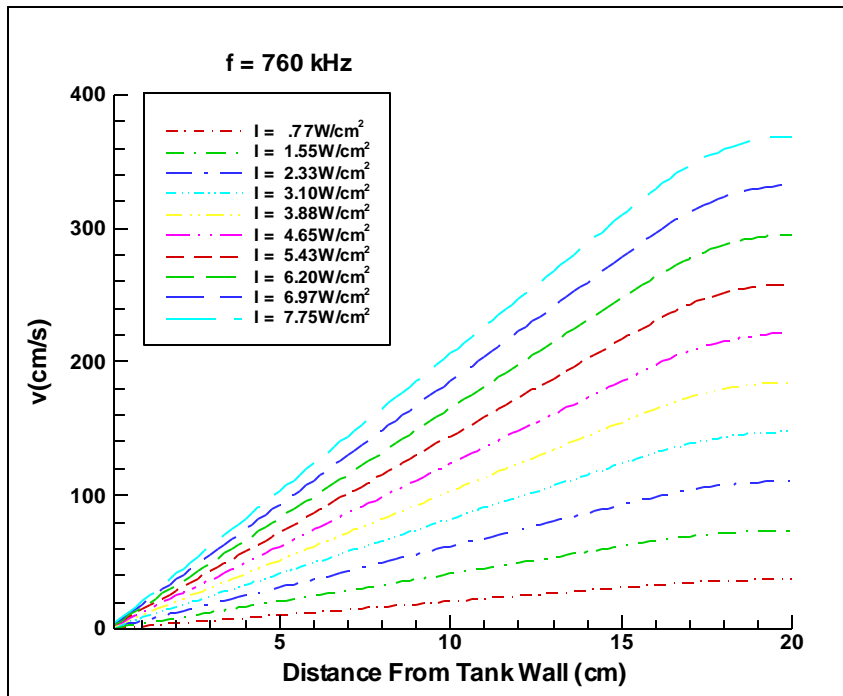
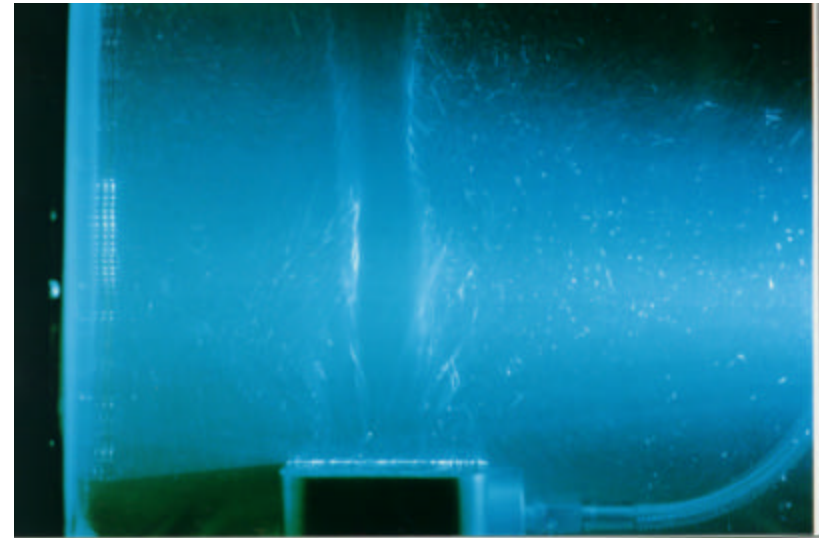
□ Megasonic power intensity:

$$I = \frac{p_0^2}{2 \rho c}$$



Megasonic Cleaning Mechanism

ACOUSTIC STREAMING



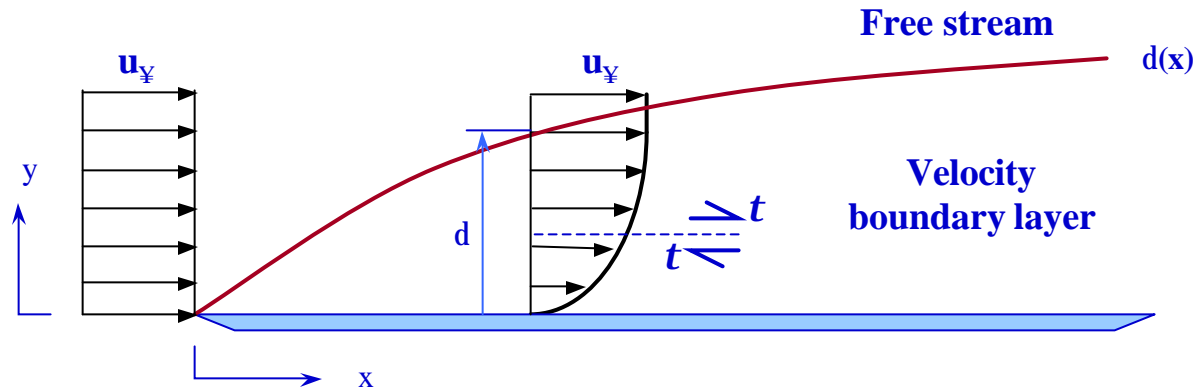
PARTICLE REMOVAL

- ❑ **Nano-scale particles will be a challenge to current cleaning techniques.**

- ❑ **The most widely used cleaning techniques:**
 - ✓ **non-contact method (megasonic cleaning)**
 - ✓ **contact cleaning method (brush scrubbers)**

- ❑ **The two basic elements that need to be understood are :**
 - ✓ **Particle Adhesion**
 - ✓ **Particle Removal**

Boundary Layer Thickness



Velocity boundary layer on a flat plate

□ Acoustic boundary layer thickness:

$$d_{ac} = \left(\frac{2n}{w} \right)^{\frac{1}{2}}$$

in water, $f=850\text{KHz}$, $\delta_{ac}=0.61\mu\text{m}$

$f=760\text{KHz}$, $\delta_{ac}=0.65\mu\text{m}$

$f=360\text{KHz}$, $\delta_{ac}=0.94\mu\text{m}$

□ The hydrodynamic boundary layer thickness:

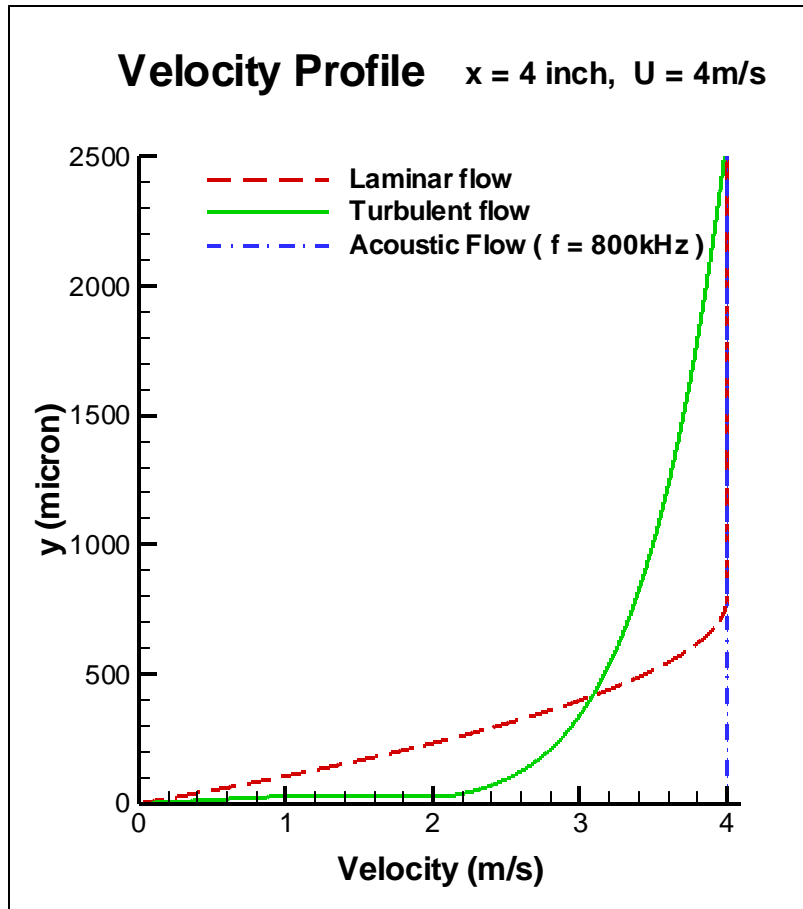
$$d_H = 0.16 \left(\frac{n}{Ux} \right)^{\frac{1}{7}} \cdot x$$

in water, $u=4\text{m/s}$, at center of the wafer,

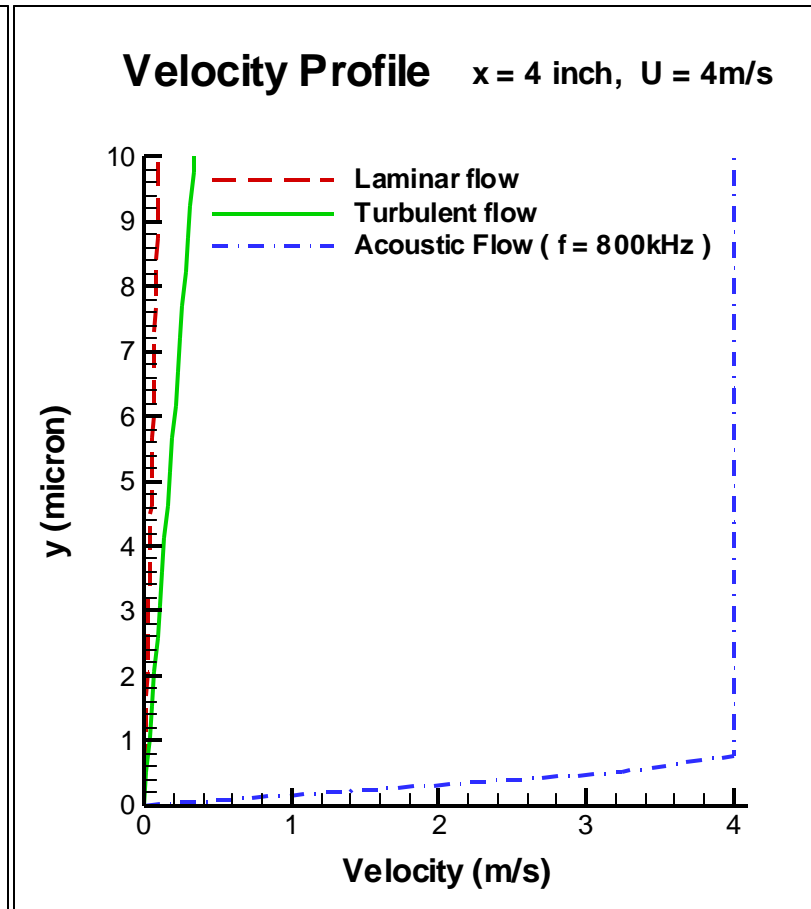
$\delta_H=2570 \mu\text{m}$

Velocity Profile in a Boundary Layer

y = 0~2500 micron



y = 0~10 micron

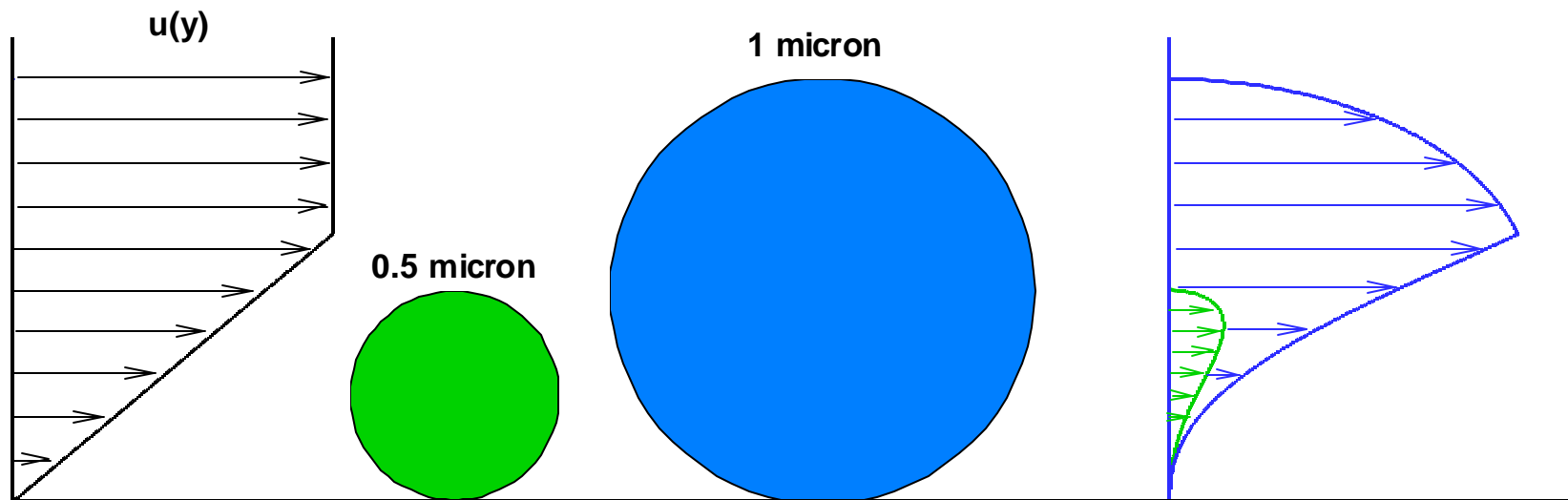


Drag Force Distribution on a Particle

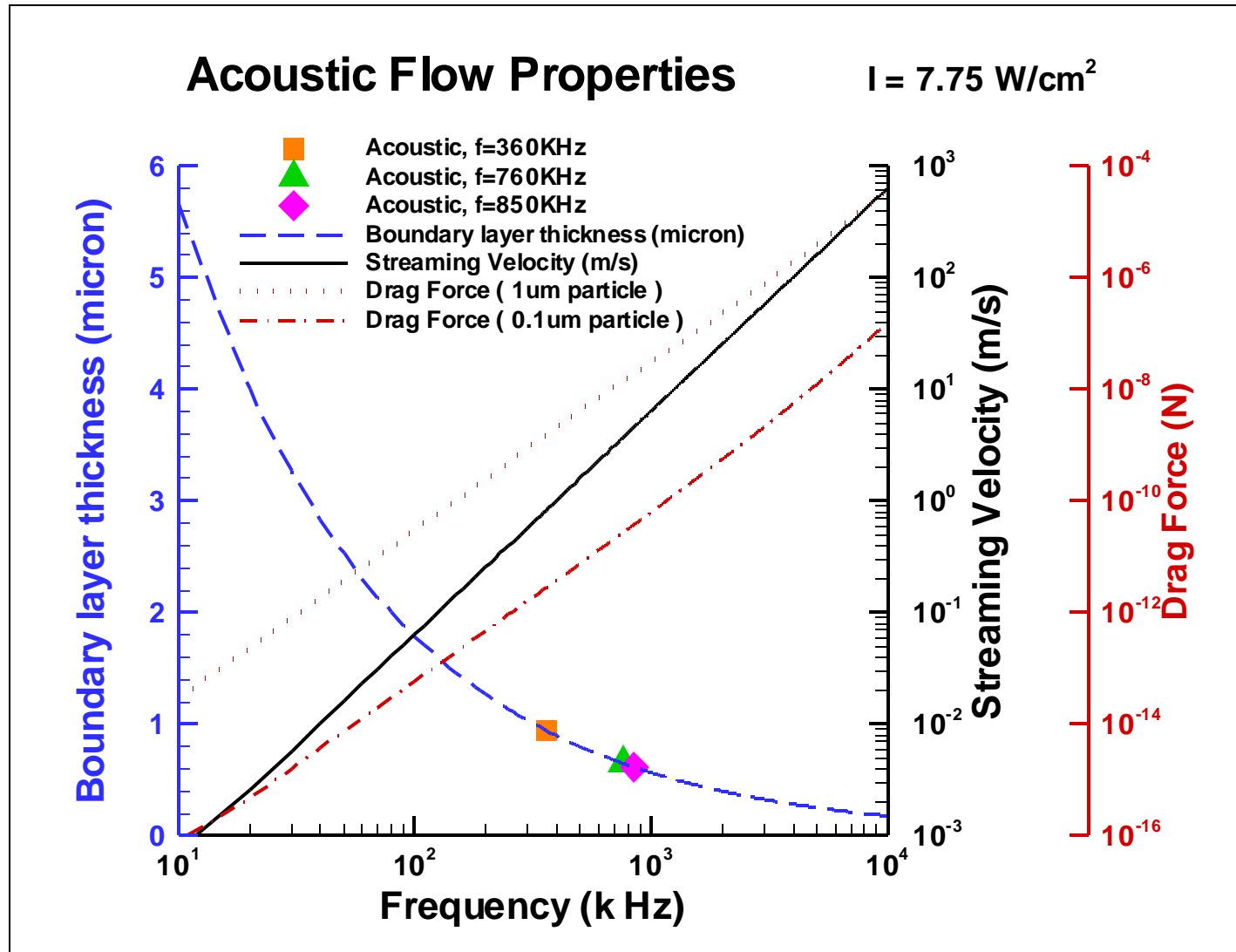
$$F_D = C_D \mathbf{r} \frac{u_i^2}{2} A_i$$

$f = 800 \text{ kHz}$, $I = 7.75 \text{ W/cm}^2$, $U_{ac} = 4.08 \text{ m/s}$
Acoustic boundary layer thickness = 0.63 micron

— $u(y)$ (m/s)
— Drag Force (0.5 micron particle)
— Drag Force (1 micron particle)



Effects of Frequency



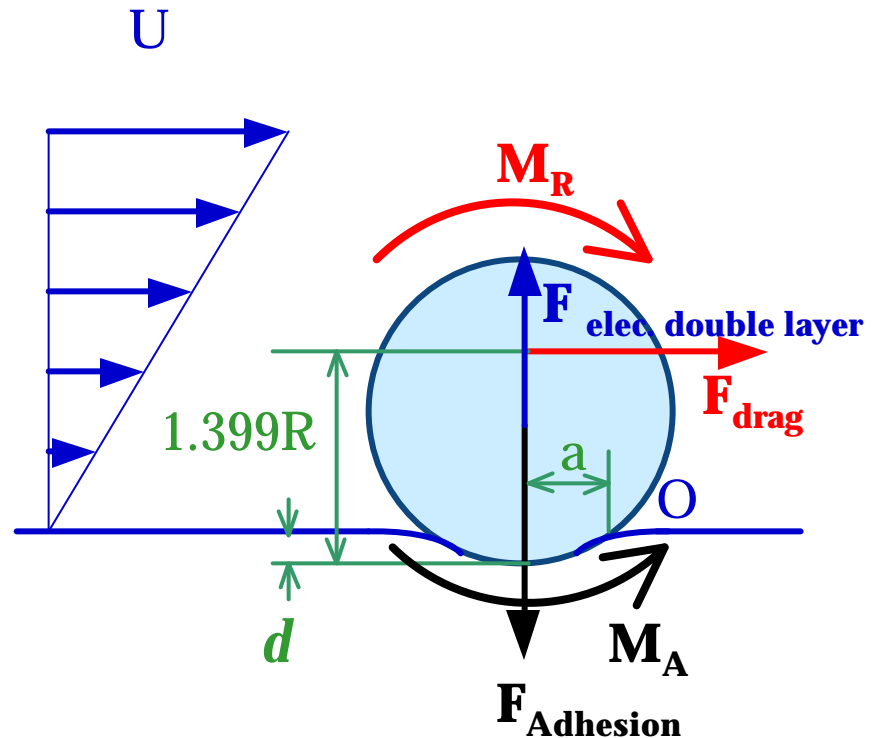
Ratio of Removal/Adhesion Moment (RM)

□ RM:

$$RM = \frac{\text{Removal moment}}{\text{Adhesion resisting moment}}$$

$$RM = \frac{F_d(1.399R - d) + F_{dl} \cdot a}{F_a \cdot a}$$

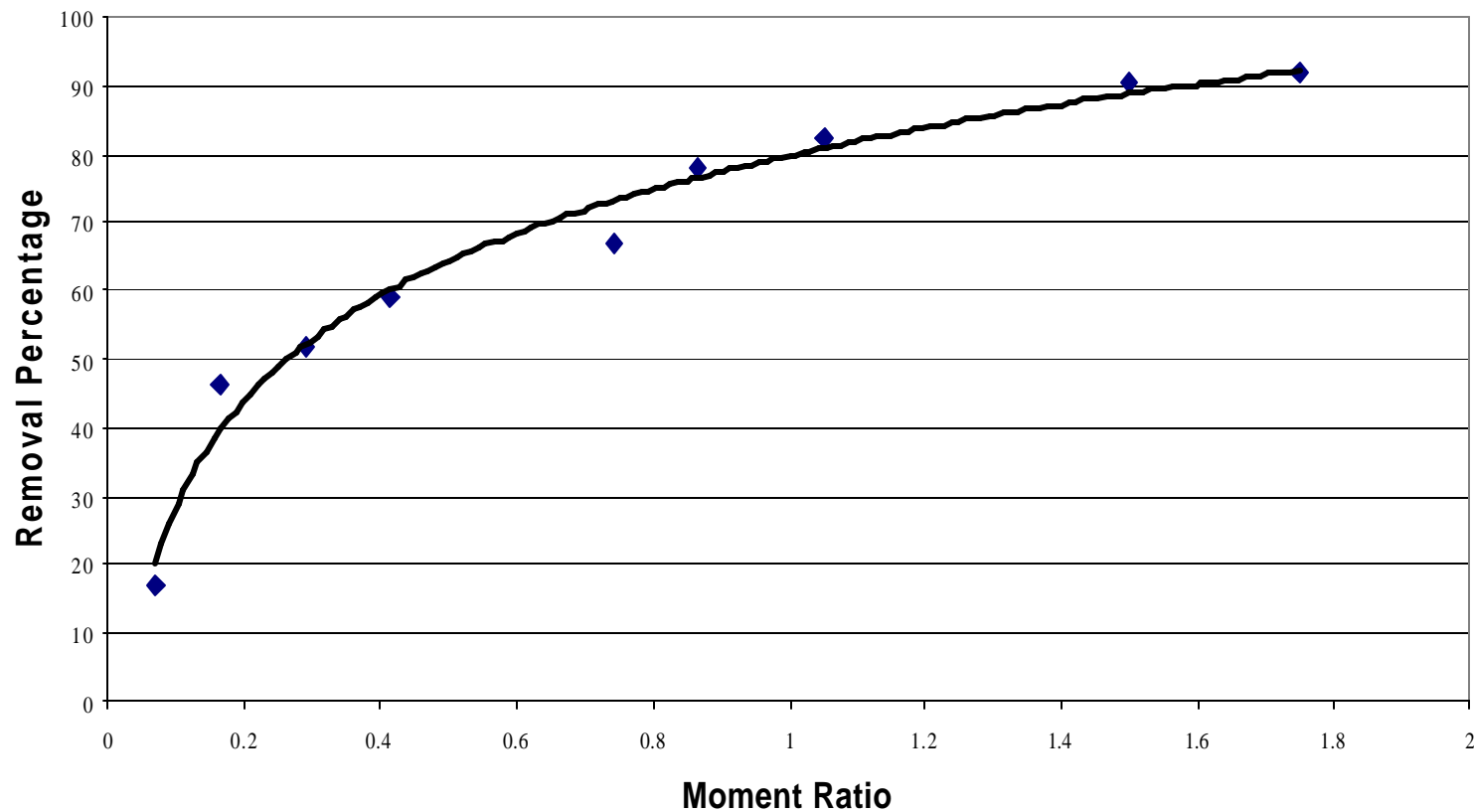
□ When $RM > 1$, most particles are removed.



Rolling removal mechanism

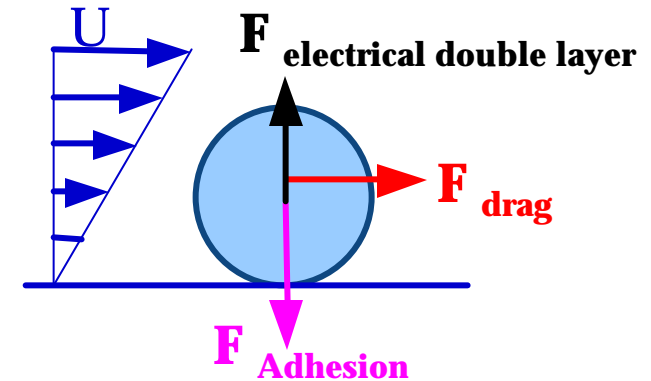
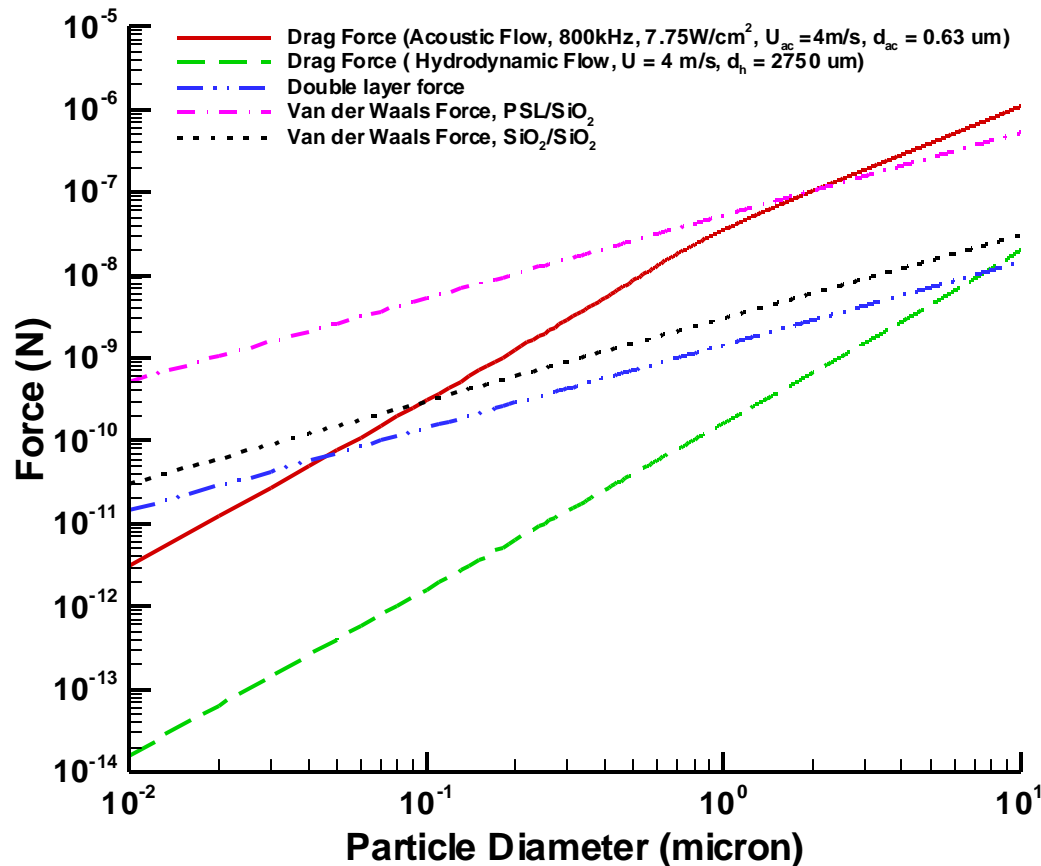
Removal Percentage vs. Moment Ratio (Silica Removal Experiment)

Removal Percentage Moment Ratio



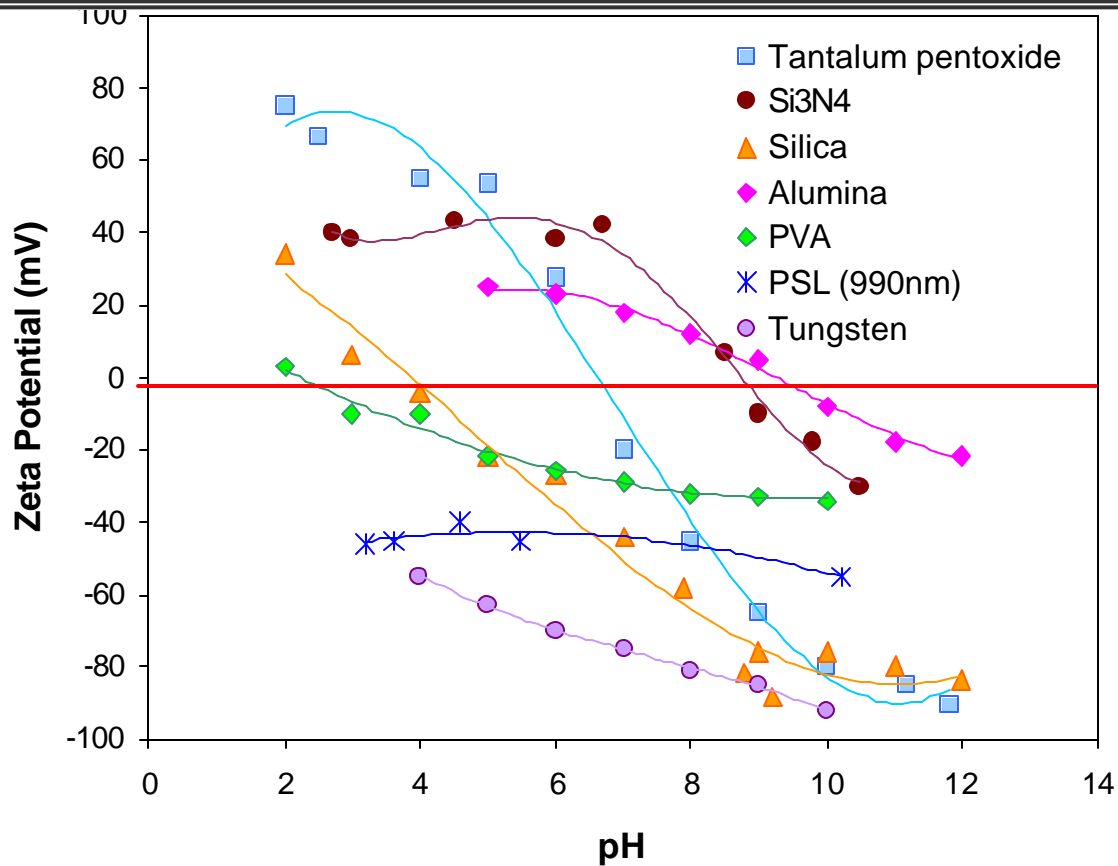
Effect of Particle Size on Adhesion and Removal Forces

Forces vs. Particle Diameter $U = 4 \text{ m/s}$



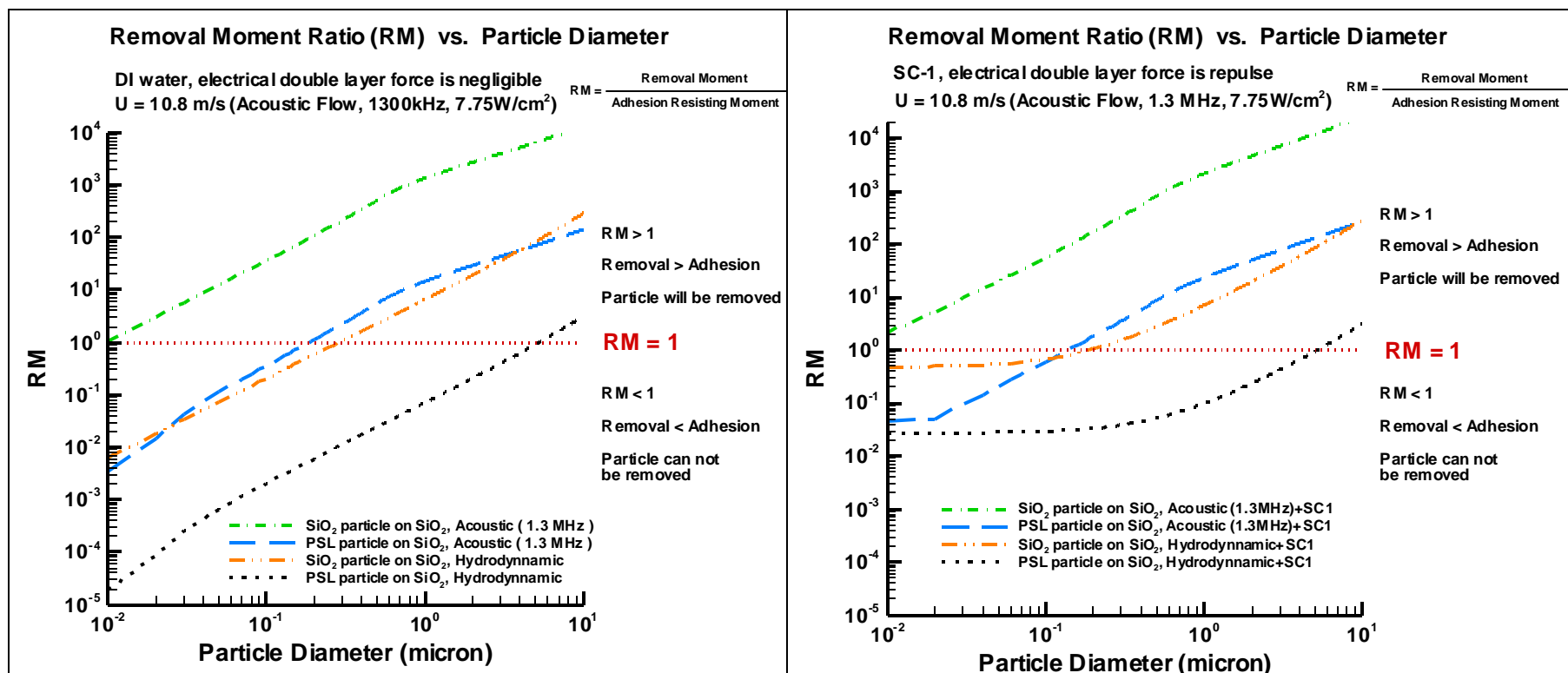
- Drag force, electrical double layer force, and adhesion force all increase with particle size.
- Acting as removal forces,
 - ❖ $d > 100 \text{ nm}$, acoustic flow drag force is dominated;
 - ❖ $30 \text{ nm} < d < 100 \text{ nm}$, drag force and electrical double layer force are on same level;
 - ❖ $d < 30 \text{ nm}$, electrical double layer force is dominated;

Electrical Double Layer Force



- At the pH of water, silica, PSL, PVA, and W particles are all negatively charged.
- The high negative zeta potentials are measured at high pH solution for SiO₂, Si₃N₄, Al₂O₃, tantalum pentoxide, tungsten, polyvinyl alcohol (PVA), and also for Si and PSL.
- Using a high pH cleaning solution, electrical double layer force occurs as a strong repulsion between the particle and the substrate.

Removal/Adhesion Moment Ratio (RM)

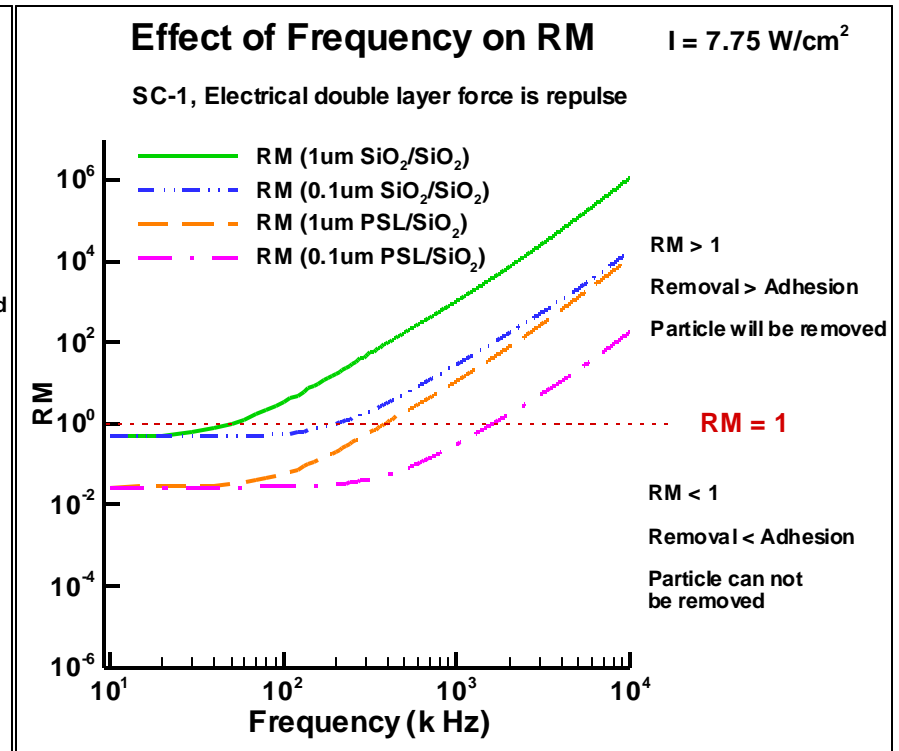
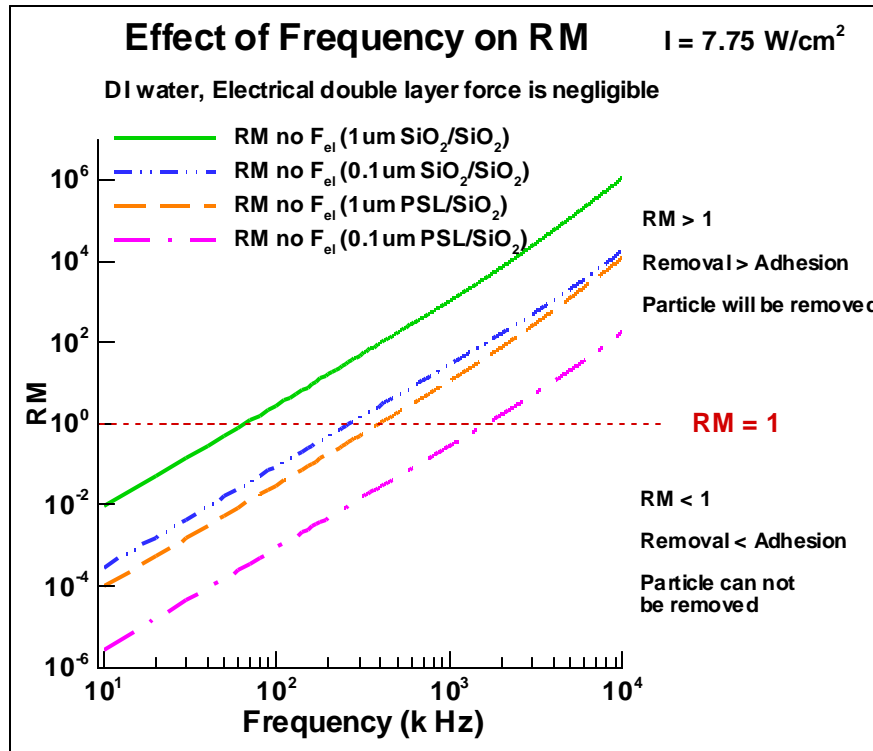


- Using DI water only, the removal of nano-size particles (10-100 nm) can be best accomplished using acoustic streaming at frequencies larger than 1.3 MHz.

Effects of Frequency on RM

DI water, Electrical double layer force is negligible

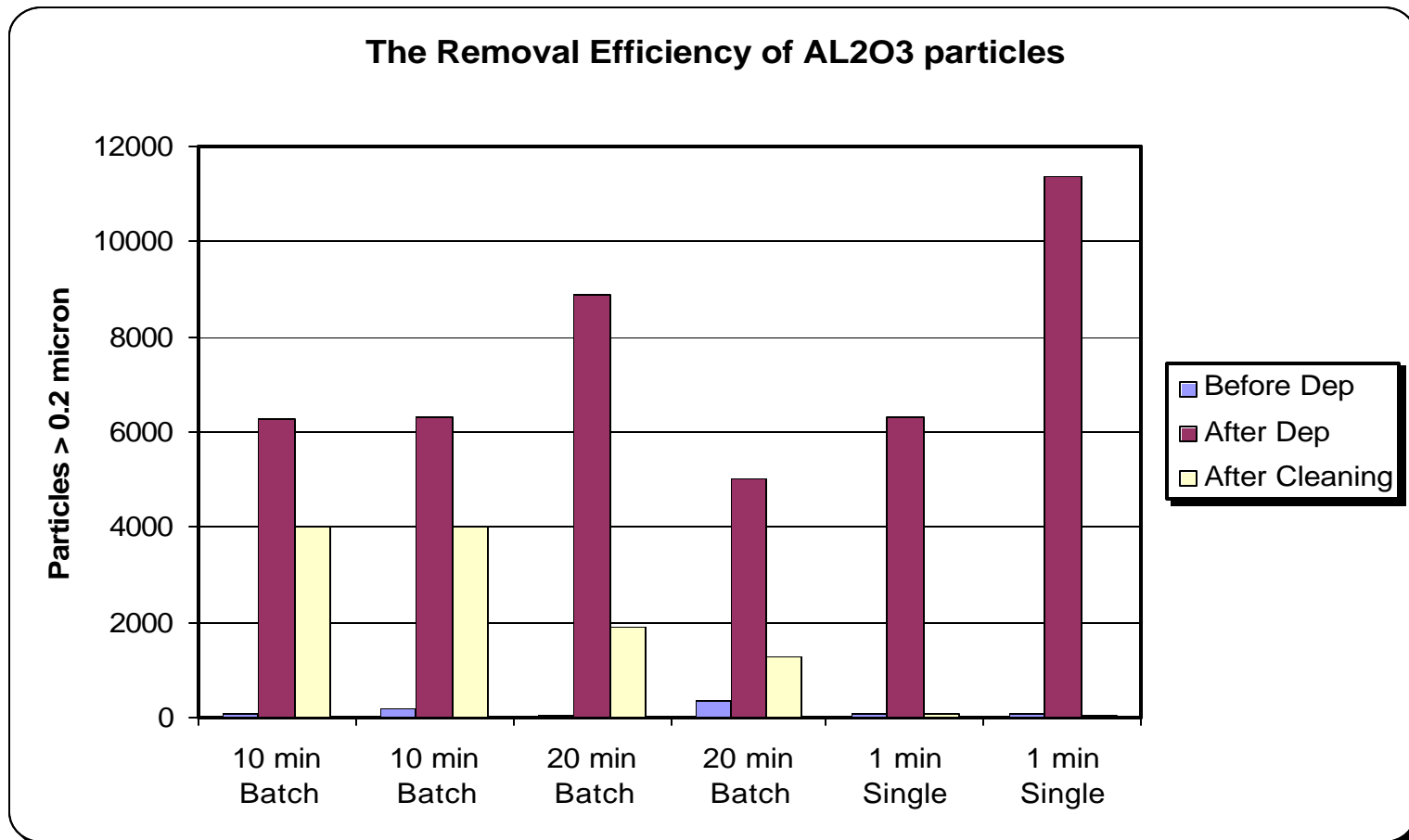
SC-1, Electrical double layer force is repulsive



- The smaller the particles, the higher frequency acoustic flow is needed.
- Soft particles (PSL) are more difficult to remove than hard particle (silica), needing almost an order of magnitude higher frequency.

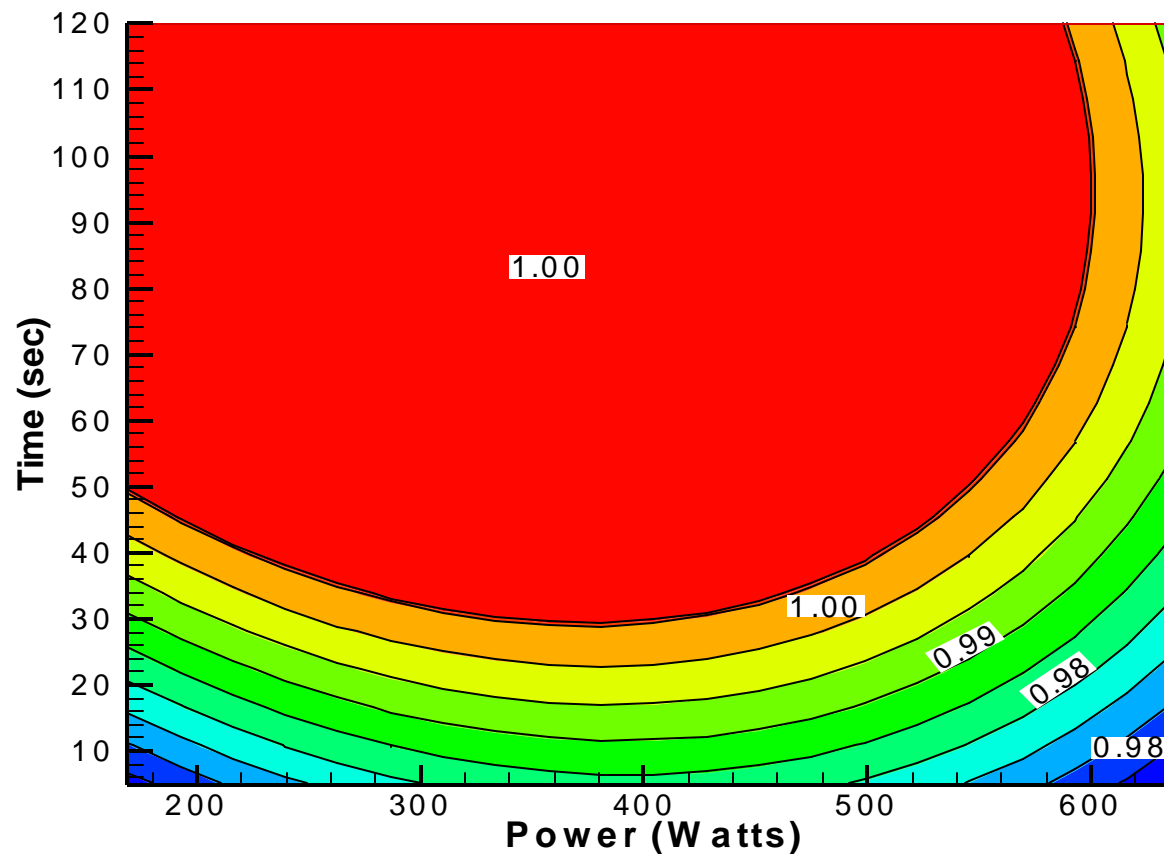
Fast Single Wafer Post-CMP Cleaning

Single versus Batch

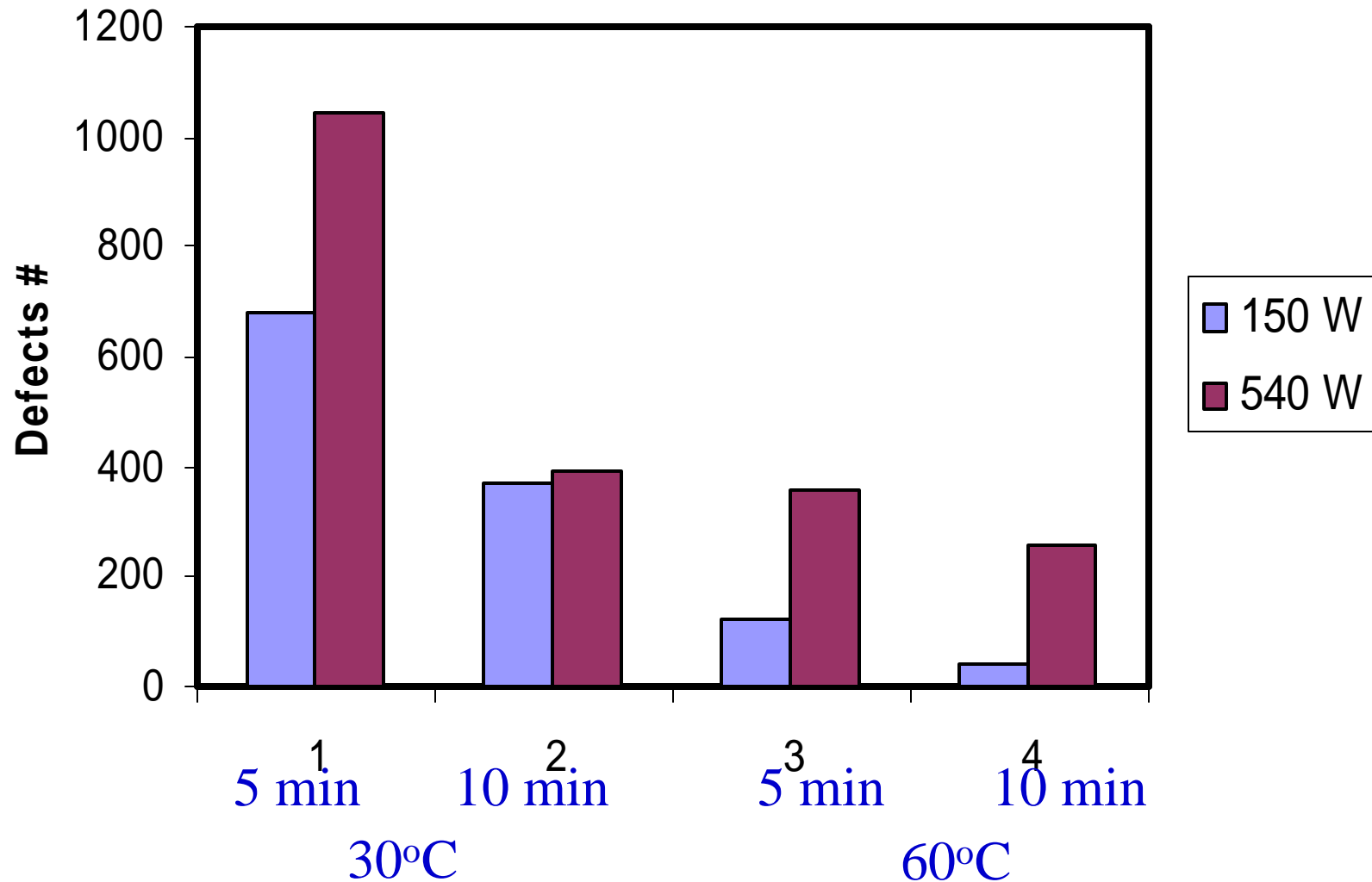


- ❖ **Complete removal of silica particles down to 100nm is achievable by using a single wafer megasonic cleaning with DI water only.**

Single Megasonic Cleaning Process, Temp = 35°C
Removal Efficiency of Silica Particles $\geq 0.1 \mu\text{m}$



Megasonic Cleaning of Polished TOX Wafers Using SC1



Key Results from Preliminary Research

- ❑ **Megasonics induced acoustic streaming is essential to the removal of submicron and nano-size particles.**
- ❑ **As the frequency increases, the acoustic boundary layer thickness decreases and streaming velocity increases thereby increasing the removal (drag) force.**
- ❑ **Using DI water, the removal of nano-size particles (10-100 nm) can be best accomplished using acoustic streaming at frequencies larger than 1.3 MHz.**
- ❑ **Utilizing the electrical double layer force as a repulse force, by using basic chemistry, removal of 10nm silica particle can be accomplished using megasonic cleaning above 800 kHz.**
- ❑ **Acting as removal forces,**
 - ❖ **$d > 100\text{nm}$, acoustic flow drag force is dominated;**
 - ❖ **$30\text{nm} < d < 100\text{nm}$, drag force and electrical double layer force are on same level;**
 - ❖ **$d < 30\text{nm}$, electrical double layer force is dominated;**
- ❑ **Soft particles (such as Polystyrene Latex PSL) are more difficult to remove than hard particle (silica), because of adhesion induced deformation, needing almost an order of magnitude higher frequency.**